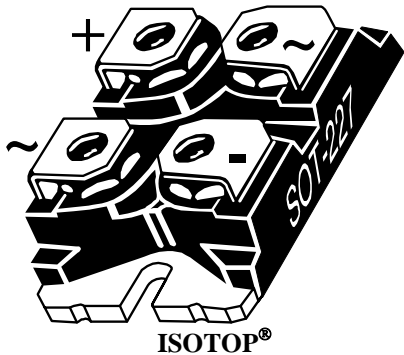
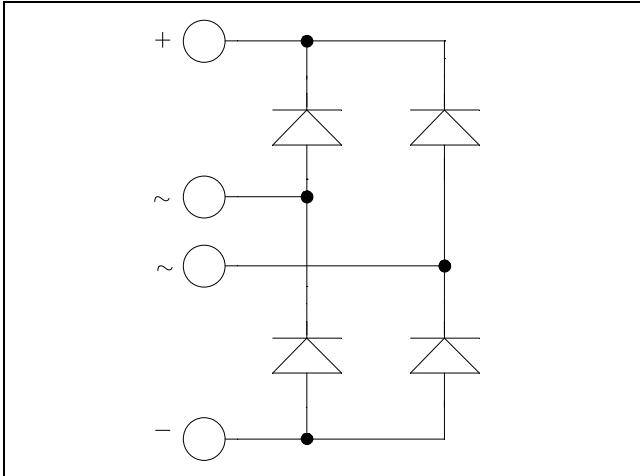


ISOTOP<sup>®</sup> SiC Diode  
Full Bridge Power Module

V<sub>RRM</sub> = 600V  
I<sub>C</sub> = 40A @ T<sub>c</sub> = 100°C



### Application

- Switch mode power supplies rectifier
- Induction heating
- Welding equipment
- High speed rectifiers

### Features

- **SiC Schottky Diode**
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V <sub>R</sub>	Maximum DC reverse Voltage	600	V
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage		
I <sub>F(AV)</sub>	Maximum Average Forward Current	40	A
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current	500	
		10 μs	T <sub>C</sub> = 25°C

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

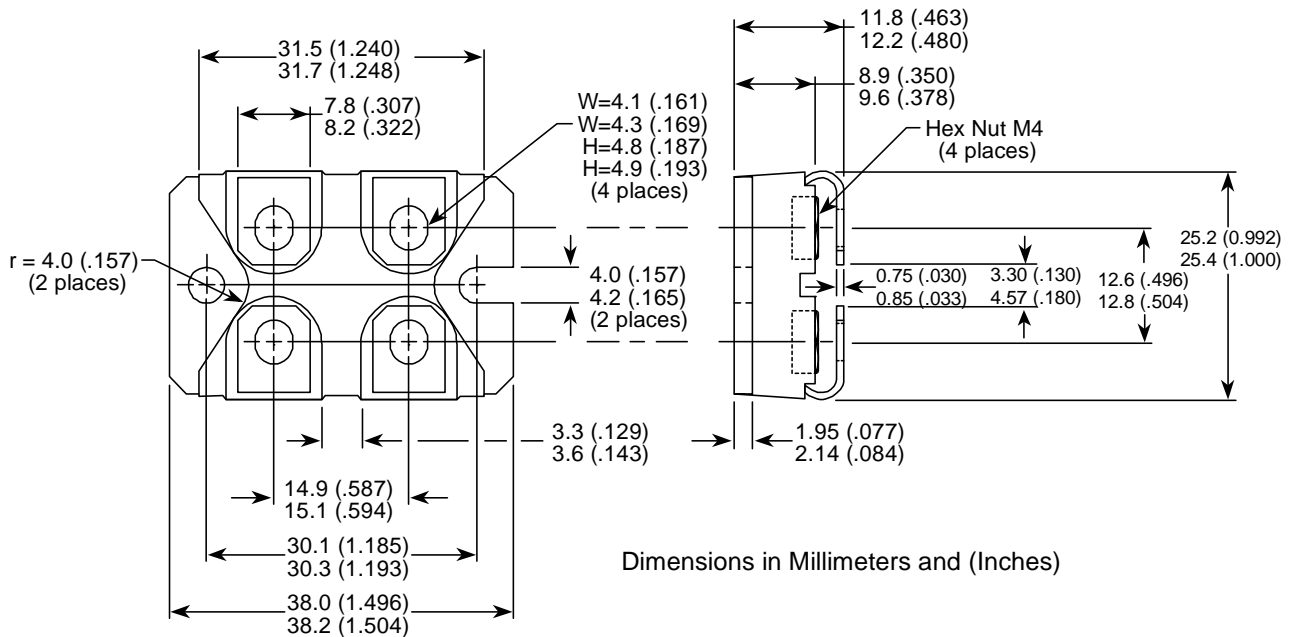
## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$V_F$	Diode Forward Voltage	$I_F = 40\text{A}$	$T_j = 25^\circ\text{C}$		1.6	1.8	V
			$T_j = 175^\circ\text{C}$		2	2.4	
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		200	800	$\mu\text{A}$
			$T_j = 175^\circ\text{C}$		400	4000	
$Q_C$	Total Capacitive Charge	$I_F = 40\text{A}, V_R = 300\text{V}$ $di/dt = 1200\text{A}/\mu\text{s}$		56		nC	
C	Total Capacitance	$f = 1\text{MHz}, V_R = 200\text{V}$		260		pF	
		$f = 1\text{MHz}, V_R = 400\text{V}$		200			

## Thermal and package characteristics

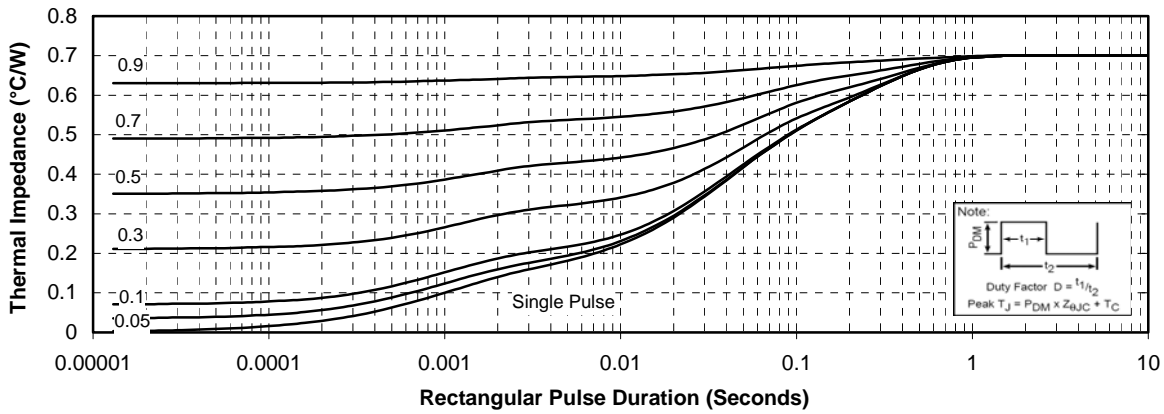
Symbol	Characteristic	Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal resistance			0.7	$^\circ\text{C}/\text{W}$
$R_{thJA}$	Junction to Ambient			20	$^\circ\text{C}/\text{W}$
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$ , $I_{isol} < 1\text{mA}$ , 50/60Hz	2500			V
$T_J, T_{STG}$	Storage Temperature Range	-55		175	$^\circ\text{C}$
$T_L$	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	$^\circ\text{C}$
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

## SOT-227 (ISOTOP®) Package Outline

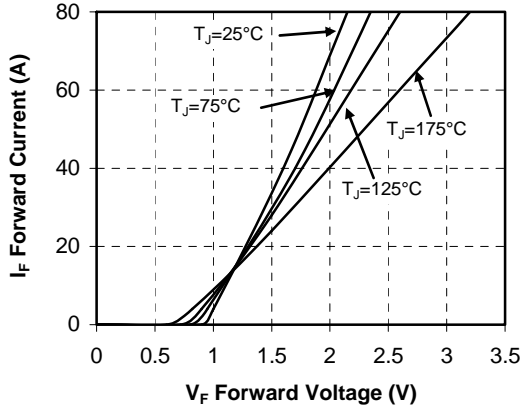


## Typical Performance Curve

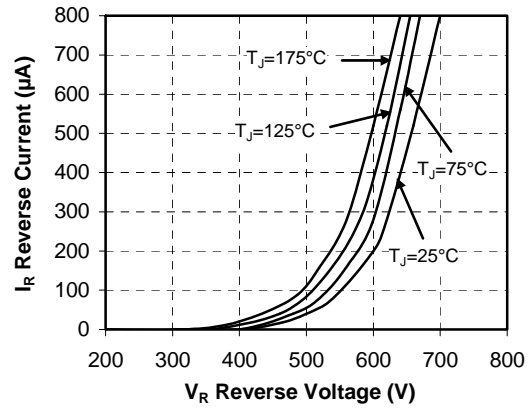
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



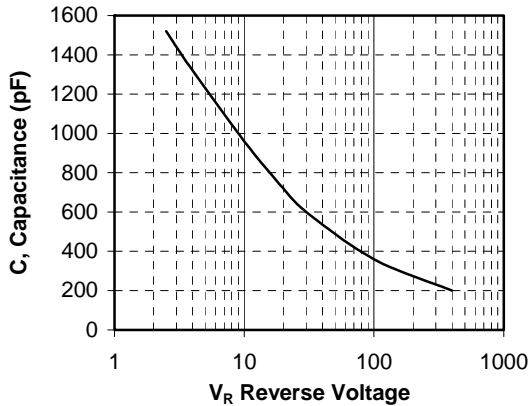
Forward Characteristics



Reverse Characteristics



Capacitance vs. Reverse Voltage



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Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.